# NPN General Purpose Transistor

The MMBT2222AM3T5G device is a spin-off of our popular SOT-23 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

#### **Features**

- Reduces Board Space
- This is a Halide-Free Device
- This is a Pb-Free Device

## **MAXIMUM RATINGS**

| Rating                         | Symbol           | Value | Unit |
|--------------------------------|------------------|-------|------|
| Collector - Emitter Voltage    | $V_{CEO}$        | 40    | Vdc  |
| Collector - Base Voltage       | V <sub>CBO</sub> | 75    | Vdc  |
| Emitter - Base Voltage         | V <sub>EBO</sub> | 6.0   | Vdc  |
| Collector Current - Continuous | Ic               | 600   | mAdc |

#### THERMAL CHARACTERISTICS

| Characteristic   | Symbol                            | Max            | Unit        |
|--|-----------------------------------|----------------|-------------|
| Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C         | P <sub>D</sub>                    | 265<br>2.1     | mW<br>mW/°C |
| Thermal Resistance, Junction-to-Ambient  | $R_{	heta JA}$                    | 470            | °C/W        |
| Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C | P <sub>D</sub>                    | 640<br>5.1     | mW<br>mW/°C |
| Thermal Resistance, Junction-to-Ambient  | $R_{\theta JA}$                   | 195            | °C/W        |
| Junction and Storage Temperature   | T <sub>J</sub> , T <sub>stg</sub> | -55 to<br>+150 | °C          |

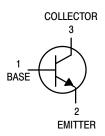
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



## ON Semiconductor®

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### MARKING DIAGRAM



SOT-723 CASE 631AA STYLE 1



AA M Specific Device CodeDate Code

#### ORDERING INFORMATION

| Device         | Package              | Shipping <sup>†</sup> |
|----------------|----------------------|-----------------------|
| MMBT2222AM3T5G | SOT-723<br>(Pb-Free) | •                     |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

| Charact  | eristic  | Symbol               | Min                                     | Max                          | Unit |
|--|--|----------------------|---|------------------------------|------|
| OFF CHARACTERISTICS  |  | •                    | •                                       | •                            | •    |
| Collector - Emitter Breakdown Voltage (I <sub>C</sub> =  | 10 mAdc, I <sub>B</sub> = 0)   | V <sub>(BR)CEO</sub> | 40                                      | -                            | Vdc  |
| Collector – Base Breakdown Voltage (I <sub>C</sub> = 10  | V <sub>(BR)CBO</sub>   | 75                   | -                                       | Vdc                          |      |
| Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μ  | V <sub>(BR)EBO</sub>   | 6.0                  | -                                       | Vdc                          |      |
| Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB</sub>  | (off) = 3.0 Vdc)   | I <sub>CEX</sub>     | -                                       | 10                           | nAdc |
| Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$  | ÷)   | I <sub>CBO</sub>     | -<br>-                                  | 0.01<br>10                   | μAdc |
| Emitter Cutoff Current ( $V_{EB} = 3.0 \text{ Vdc}, I_{C} = 0$   | 0)   | I <sub>EBO</sub>     | -                                       | 100                          | nAdc |
| Base Cutoff Current ( $V_{CE} = 60 \text{ Vdc}, V_{EB(off)}$   | = 3.0 Vdc)   | I <sub>BL</sub>      | -                                       | 20                           | nAdc |
| ON CHARACTERISTICS   |  |                      |   |                              |      |
| DC Current Gain $ \begin{aligned} &(I_C=0.1 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ &(I_C=1.0 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ &(I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \\ &(I_C=10 \text{ mAdc, } V_{CE}=10 \text{ Vdc}, T_A \\ &(I_C=150 \text{ mAdc, } V_{CE}=10 \text{ Vdc}) \text{ (Note of the constraints)} \\ &(I_C=150 \text{ mAdc, } V_{CE}=1.0 \text{ Vdc}) \text{ (Note of the constraints)} \end{aligned} $  | lote 3)<br>Note 3)   | h <sub>FE</sub>      | 35<br>50<br>75<br>35<br>100<br>50<br>40 | -<br>-<br>-<br>300<br>-<br>- | 1    |
| Collector – Emitter Saturation Voltage (Note ( $I_C$ = 150 mAdc, $I_B$ = 15 mAdc) ( $I_C$ = 500 mAdc, $I_B$ = 50 mAdc)   | V <sub>CE(sat)</sub>   | -<br>-               | 0.3<br>1.0                              | Vdc                          |      |
| Base – Emitter Saturation Voltage (Note 3) $(I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc})$ $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$   | V <sub>BE(sat)</sub>   | 0.6<br>-             | 1.2<br>2.0                              | Vdc                          |      |
| SMALL-SIGNAL CHARACTERISTICS   |  |                      |   |                              |      |
| Current – Gain – Bandwidth Product (Note 4) $(I_C = 20 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 6)$  |  | f⊤                   | 300                                     | -                            | MHz  |
| Output Capacitance ( $V_{CB} = 10 \text{ Vdc}, I_E = 0, f$   | = 1.0 MHz)   | C <sub>obo</sub>     | -                                       | 8.0                          | pF   |
| Input Capacitance ( $V_{EB} = 0.5 \text{ Vdc}$ , $I_{C} = 0$ , f   | = 1.0 MHz)   | C <sub>ibo</sub>     | -                                       | 25                           | pF   |
| Input Impedance (I <sub>C</sub> = 1.0 mAdc, $V_{CE}$ = 10 Vdc, f = (I <sub>C</sub> = 10 mAdc, $V_{CE}$ = 10 Vdc, f =   | h <sub>ie</sub>  | 2.0<br>0.25          | 8.0<br>1.25                             | kΩ                           |      |
| Voltage Feedback Ratio $ (I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = \\ (I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = \\ $  | h <sub>re</sub>  | -<br>-               | 8.0<br>4.0                              | X 10 <sup>-4</sup>           |      |
| $Small-Signal Current Gain \\ (I_C = 1.0 \text{ mAdc, } V_{CE} = 10 \text{ Vdc, } f = \\ (I_C = 10 \text{ mAdc, } V_{CE} = 10 \text{ Vdc, } f = \\ \end{cases}$  | h <sub>fe</sub>  | 50<br>75             | 300<br>375                              | -                            |      |
| Output Admittance $ (I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = \\ (I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = \\ $   | h <sub>oe</sub>  | 5.0<br>25            | 35<br>200                               | μmhos                        |      |
| Collector Base Time Constant<br>(I <sub>E</sub> = 20 mAdc, V <sub>CB</sub> = 20 Vdc, f = | rb, C <sub>c</sub>   | _                    | 150                                     | ps                           |      |
| Noise Figure ( $I_C$ = 100 $\mu$ Adc, $V_{CE}$ = 10 Vdc,   | NF   | -                    | 4.0                                     | dB                           |      |
| SWITCHING CHARACTERISTICS  |  |                      |   |                              |      |
| Delay Time   | (V <sub>CC</sub> = 30 Vdc, V <sub>BE(off)</sub> = -0.5 Vdc,                              | t <sub>d</sub>       | _                                       | 10                           |      |
|  | $I_C = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$                                      | t <sub>r</sub>       | -                                       | 25                           | ns   |
| Rise Time  |  | •                    |   |                              |      |
| Rise Time Storage Time   | $(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc}, I_{B1} = I_{B2} = 15 \text{ mAdc})$ | t <sub>s</sub>       | _                                       | 225                          | ns   |

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
 f<sub>T</sub> is defined as the frequency at which |h<sub>fe</sub>| extrapolates to unity.

## **SWITCHING TIME EQUIVALENT TEST CIRCUITS**

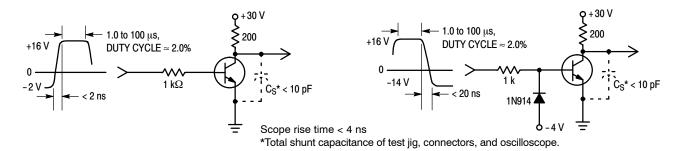


Figure 1. Turn-On Time

Figure 2. Turn-Off Time

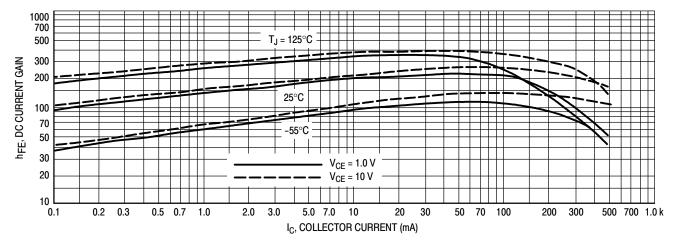


Figure 3. DC Current Gain

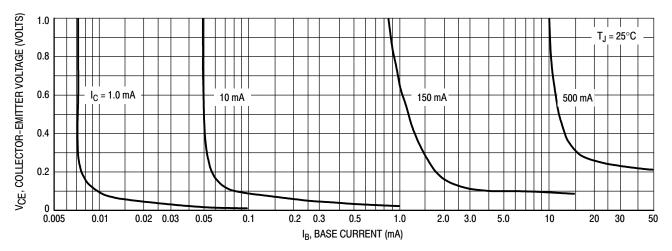


Figure 4. Collector Saturation Region

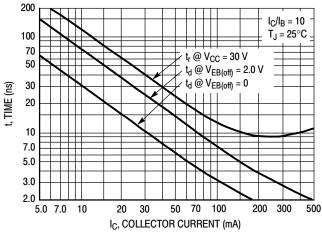


Figure 5. Turn-On Time

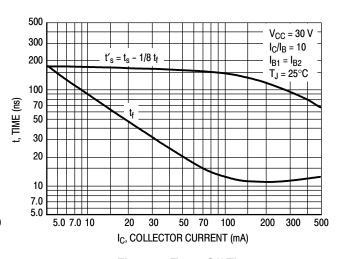


Figure 6. Turn - Off Time

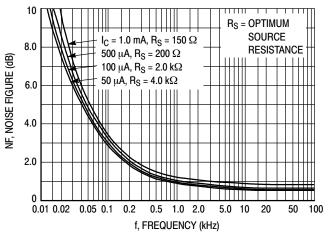


Figure 7. Frequency Effects

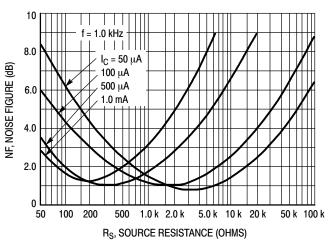


Figure 8. Source Resistance Effects

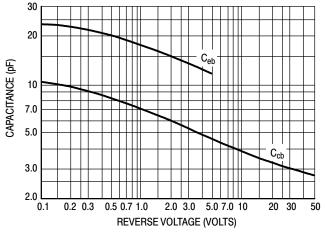


Figure 9. Capacitances

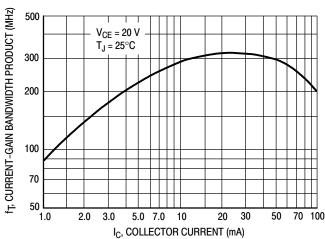
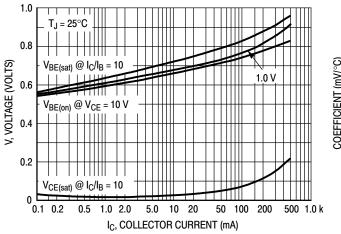


Figure 10. Current-Gain Bandwidth Product



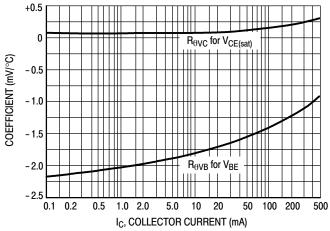
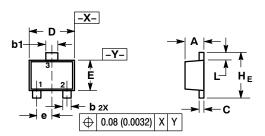


Figure 11. "On" Voltages

Figure 12. Temperature Coefficients

### PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 ISSUE C



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

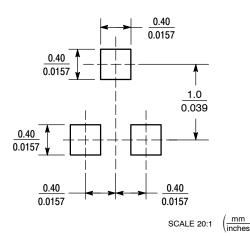
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

  DIMENSIONS D AND E DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS.

|     | MILLIMETERS |      |      | INCHES |          |        |  |
|-----|-------------|------|------|--------|----------|--------|--|
| DIM | MIN         | NOM  | MAX  | MIN    | NOM      | MAX    |  |
| Α   | 0.45        | 0.50 | 0.55 | 0.018  | 0.020    | 0.022  |  |
| b   | 0.15        | 0.21 | 0.27 | 0.0059 | 0.0083   | 0.0106 |  |
| b1  | 0.25        | 0.31 | 0.37 | 0.010  | 0.012    | 0.015  |  |
| С   | 0.07        | 0.12 | 0.17 | 0.0028 | 0.0047   | 0.0067 |  |
| D   | 1.15        | 1.20 | 1.25 | 0.045  | 0.047    | 0.049  |  |
| Е   | 0.75        | 0.80 | 0.85 | 0.03   | 0.032    | 0.034  |  |
| е   | 0.40 BSC    |      |      | (      | 0.016 BS | С      |  |
| ΗE  | 1.15        | 1.20 | 1.25 | 0.045  | 0.047    | 0.049  |  |
| L   | 0.15        | 0.20 | 0.25 | 0.0059 | 0.0079   | 0.0098 |  |

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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